

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PATENT APPLICATION

Inventors: Pooran Chandra Joshi, Apostolos T.
Voutsas, and John W. Hartzell

Serial No: Not Yet Assigned

Attorney Docket No.
SLA0786

Filed: Herewith

Title: HIGH DENSITY PLASMA PROCESS
FOR THE FORMATION OF SILICON
DIOXIDE ON SILICON CARBIDE
SUBSTRATES

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

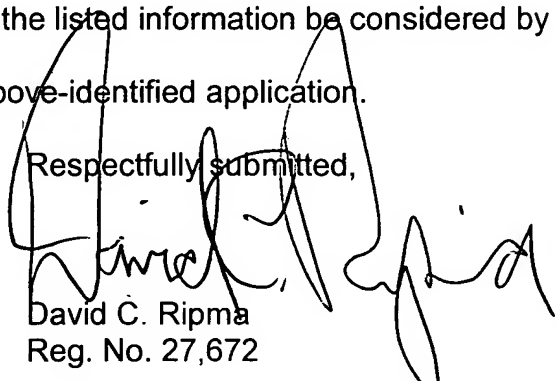
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

March 29, 2004
(Date)

Respectfully submitted,


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Disclosure SLA0786

